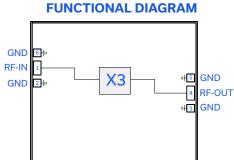


Mini-Circuits

### 50Ω Output 40 to 72 GHz

### THE BIG DEAL

- Wideband Output Frequency: 40 to 72 GHz
- Excellent Fundamental and Harmonic Suppression:
  - F1: 41 dBc Typ.
  - F2: 33 dBc Typ.
  - F4: 33 dBc Typ.
- Input Drive Level: +12 to +19 dBm
- Conversion Loss: 21.1 dB Typ.



SEE ORDERING INFORMATION ON THE LAST PAGE

### **APPLICATIONS**

- Test and Measurement Equipment
- 5G MIMO and Back Haul Radio Systems
- Satellite Communications
- Radar, EW, and ECM Defense Systems

### **PRODUCT OVERVIEW**

Mini-Circuits' CY3-723-D+ is a wideband MMIC Frequency Tripler, converting input frequencies from 13.3 to 24 GHz into output frequencies from 40 to 72 GHz. Its wide output range makes this model suitable for broadband systems as well as a wide variety of narrow-band applications. The CY3-723-D+ die utilizes GaAs HBT technology and is suitable for chip and wire assemblies.

### **KEY FEATURES**

Features	Advantages	
Broadband, 40 to 72 GHz output	With an output frequency range spanning 40 to 72 GHz, this multiplier supports broadband applications such as defense and instrumentation as well as a wide range of narrowband system requirements including 5G.	
<ul> <li>Excellent Fundamental and Harmonic Suppression:</li> <li>F1, 41 dBc Typ.</li> <li>F2, 33 dBc Typ.</li> <li>F4, 33 dBc Typ.</li> </ul>	Harmonic and fundamental filtering requirements are dramatically simplified due to the high suppression resulting from internal cancellation within the diode configuration.	
Wide input power range, +12 to +19 dBm	Wide input power signal range accommodates different input signal levels while still maintain low conversion loss.	
Unpackaged Die	Enables integration into hybrid chip and wire assemblies.	

REV. A

**MMIC DIE** 

### X3 Frequency Multiplier **CY3-723-D+**

Mini-Circuits

### 50Ω Output 40 to 72 GHz

### **ELECTRICAL SPECIFICATIONS<sup>1,3</sup> AT +25°C AND Z**<sub>0</sub> = 50Ω, UNLESS NOTED OTHERWISE

Para	meter	Input Frequency (GHz)	Min	Тур.	Max.	Unit
Multiplication Factor				3		
Frequency Range, Input (F1)			13.33	-	22.33	GHz
Frequency Range, Ou	itput (F3)		40	-	72	GHz
Input Power			+12	+18	+19	dBm
Conversion Loss (F3)		13.3 - 15		20.5		dB
		15 - 16.6		19.5		
		16.6 - 18.3		20.1		
		18.3 - 20		21.7		
		20 - 22.3		23.6		
		22.3 - 24		25.0		
		13.3 - 15		50		dBc
		15 - 16.6		50		
	F1	16.6 - 18.3		42		
	FI	18.3 - 20		36		
		20 - 22.3		30		
		22.3 - 24		28		
		13.3 - 15		49		dBc
	F2	15 - 16.6		41		
Harmonic Output <sup>2</sup>		16.6 - 18.3		31		
		18.3 - 20		25		
		20 - 22.3		22		
		22.3 - 24		19		
	F4	13.3 - 15		31		dBc
		15 - 16.6		42		
		16.6 - 18.3		31		
		18.3 - 20		36		
		20 - 22.3		28		
		22.3 - 24		28		

1. Measured on Mini-Circuits Die Evaluation board. See Figure 3 for test conditions.

2. Harmonics of input frequency below the power of desired output F3.

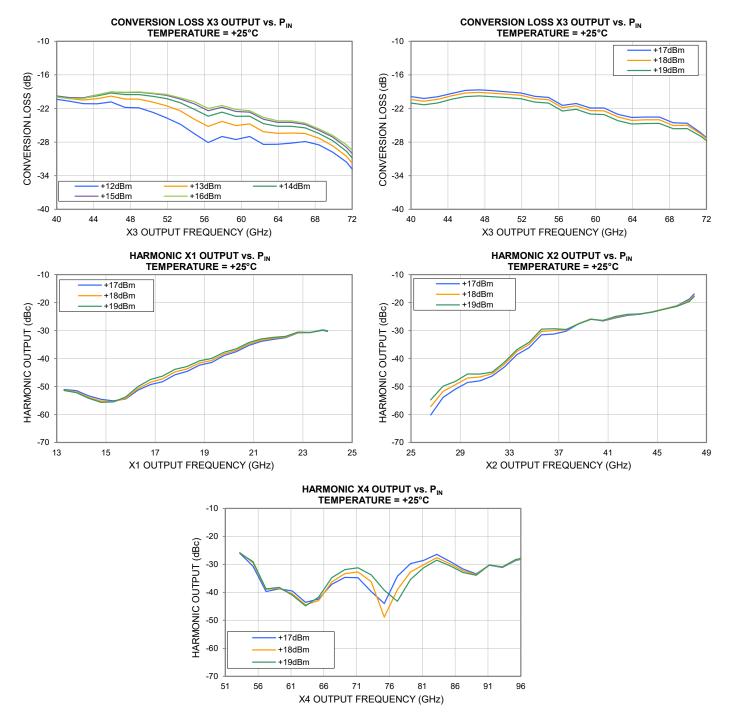
3. All specifications are measured with RF input power = +18 dBm.



Mini-Circuits

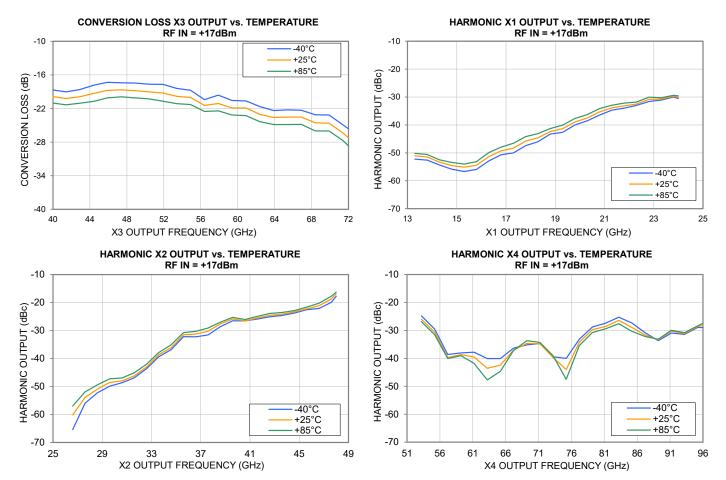
# X3 Frequency Multiplier **CY3-723-D+**

50Ω Output 40 to 72 GHz



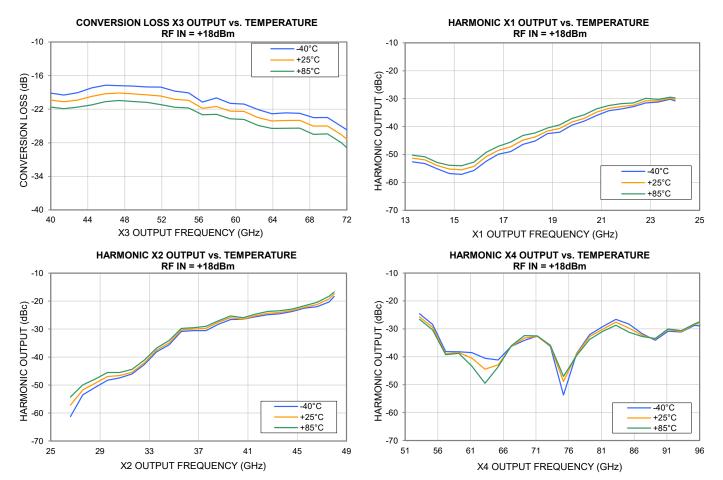


50Ω Output 40 to 72 GHz





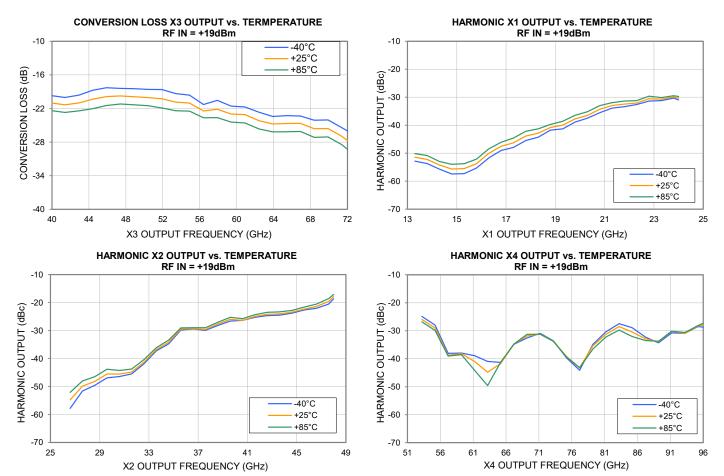
50Ω Output 40 to 72 GHz





**Mini-Circuits** 50Ω Output 40 to 72 GHz

**MMIC DIE** 





Mini-Circuits

X

50 $\Omega$  Output 40 to 72 GHz

### **ABSOLUTE MAXIMUM RATINGS<sup>4</sup>**

Parameter	Ratings	
Operating Temperature⁵	-40°C to +85°C	
Storage Temperature (for Die) <sup>6</sup>	-65°C to +150°C	
RF Input Power	+22 dBm	
Junction Temperature <sup>7</sup>	+150°C	

 Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

5. Bottom of Die.

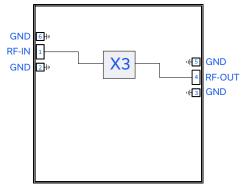
For die shipped in Gel-Pak see ENV-80 (limited by packaging).

7. Hot spot temperature on die.



Mini-Circuits 50Ω Output 40 to 72 GHz

### **FUNCTIONAL DIAGRAM**



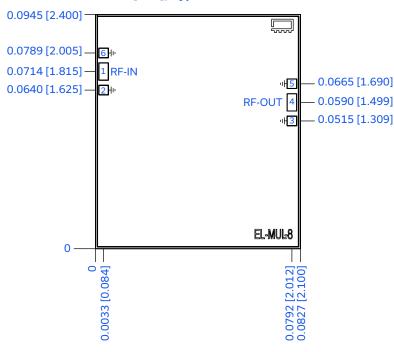
**MMIC DIE** 

#### Figure 1. CY3-723-D+ Functional Diagram

### **PAD DESCRIPTION**

Function	Pad #	Description (Refer to Figure 1)	
RF-IN	1	Connect to RF Input.	
RF-OUT	4	Connect to RF Output.	
GND	2, 3, 5 & 6	Connected to die backside through vias. Bond wires to ground are optional.	

### **DIE OUTLINE: inches [mm], Typical**



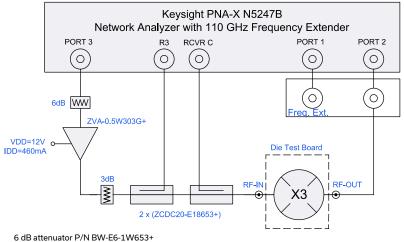
### **DIMENSIONS:** inches [mm], Typical

Die Size	0.0827 x 0.0945 [2.100 x 2.400]
Die Thickness	0.0040 [0.100]
Bond Pad Sizes:	
Pads 1 & 4	0.0036 x 0.0068 [0.092 x 0.172]
Pad 2, 3, 5 & 6	0.0036 x 0.0036 [0.092 x 0.092]
Plating (Pads & Bottom of Die)	Gold

Figure 2. CY3-723-D+ Die Outline



### **APPLICATION AND CHARACTERIZATION SETUP**



3 dB attenuator P/N BW-E0-1W053+

Figure 3. Application and Characterization Setup for CY3-723-D+

#### **TEST PARAMETERS AND CONDITIONS**

DUT attached on a Mini-Circuits Die Characterization Test Board. Conversion Loss and Harmonic Output are measured using PNA-X Network Analyzer.

Test Conditions: For Conversion Loss and Harmonic Rejection: RF input power: +12 to +19 dBm.



Mini-Circuits 50Ω Output 40 to 72 GHz

**MMIC DIE** 

### ASSEMBLY DIAGRAM

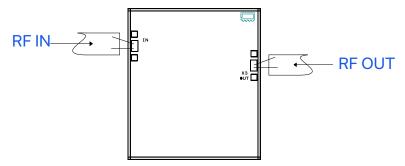


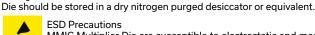
Figure 4. CY3-723-D+ Assembly Diagram

- Bond wire diameter: 1 mil
- Bond wire lengths from Die Pad to PCB at RF-IN & RF-OUT ports: 11 ± 1 mils
- Typical Gap from Die edge to PCB edge: 3 mils
- PCB thickness and material: 3.5 mils (Thickness: 0.5 oz copper on each side).

### ASSEMBLY AND HANDLING PROCEDURE

1. Storage

2.



MMIC Multiplier Die are susceptible to electrostatic and mechanical damage. Die are supplied in anti-static protected material, which should be opened only in clean room conditions at an appropriately grounded anti-static workstation.

3. Die Handling and Attachment

Devices require careful handling using tools appropriate for manipulating semiconductor chips. It is recommended to handle the chips along the edges with a custom designed collet. The surface of the chips have exposed air bridges and should not be touched with a vacuum collet, tweezers or fingers. The die mounting surface must be clean and flat. Using conductive silver-filled epoxy, apply sufficient adhesive to meet the required bond line thickness, fillet height and coverage around the total periphery of the device. The recommended epoxy is Ablestik 84-1 LMISR4 or equivalent. Parts should be cured in a nitrogen-filled atmosphere per manufacturer's recommended cure profile.

4. Wire Bonding

Openings in the surface passivation above the gold bond pads are provided to allow wire bonding to the die. Thermosonic bonding is recommended with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. The suggested interconnect is pure gold, 1 mil diameter wire . Bonds are recommended to be made from the bond pads on the die to the package or substrate. All bond wire length and bond wire height should be kept as short as possible, unless specified by design, to minimize performance degradation due to undesirable series inductance.

### Mini-Circuits



### **MMIC DIE**

### X3 Frequency Multiplier **CY3-723-D+**

Mini-Circuits

### 50Ω Output 40 to 72 GHz

### ADDITIONAL DETAILED INFORMATION IS AVAILABLE ON OUR DASHBOARD

Performance Data	Table			
	Graphs			
Case Style	Die			
RoHs Status	Compliant			
	Quantity, Package	Model No.		
	Gel - Pak: 5, 10, 50, KGD*	CY3-723-DG+		
Die Ordering and Packaging Information	Medium†, Partial wafer: <460	CY3-723-DP+		
	Full wafer <sup>†</sup>	CY3-723-DF+		
	<sup>†</sup> Available upon request contact sales representative. Refer to <u>AN-60-067</u>			
Die Marking	EL-MUL-8			
Environmental Ratings	ENV-80			

\*Known Good Die ("KGD") means that the die in question have been subjected to Mini-Circuits DC test performance criteria and measurement instructions and that the parametric data of such die fall within a predefined range. While DC testing is not definitive, it does provide a higher degree of confidence that die are capable of meeting typical RF electrical parameters specified by Mini-Circuits.

Notes

A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.

B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuits' applicable established test performance criteria and measurement instructions.

C. The parts covered by this specification document are subject to Mini-Circuits' standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained there in. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/MCLStore/terms.jsp

D. Mini-Circuits does not warrant the accuracy or completeness of the information, text, graphics and other items contained within this document and same are provided as an accommodation and on an As is basis, with all faults.

E. Purchasers of this part are solely responsible for proper storing, handling, assembly and processing of known good die (KGD) (including, without limitation, proper ESD preventative measures, die preparation, die attach, wire bonding and related assembly and test activities), and Mini-Circuits assumes no responsibility therefor or for environmental effects on KGD.

F. Mini-Circuits and the Mini-Circuits logo are registered trademarks of Scientific Components Corporation d/b/a Mini-Circuits. All other third-party trademarks are the property of their respective owners. A reference to any thirdparty trademark does not constitute or imply any endorsement, affiliation, sponsorship, or recommendation by any such third-party of Mini-Circuits or its products.

